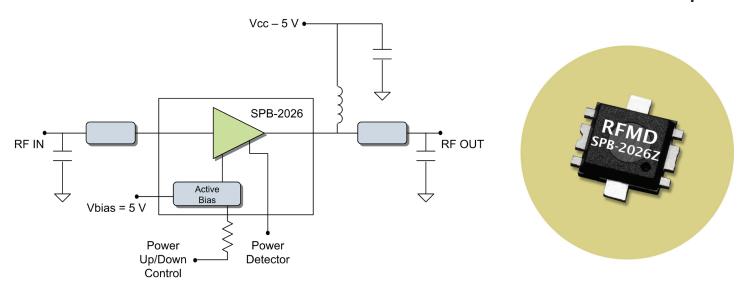
RFMD® SPB-2026Z

0.7 GHz to 2.2 GHz 2W InGaP Amplifier



The SPB-2026Z is a high-performance, high-linearity 0.7 GHz to 2.2 GHz 2 watt single-stage Class AB heterojunction bipolar transistor (HBT) amplifier, housed in a surface-mountable, plastic encapsulated package. This InGaP amplifier is well suited for use as a driver stage in macro/micro-cell infrastructure equipment, or as the final output stage in pico-cell infrastructure equipment. It is prematched to approximately 5 ohms at the RF input for broadband performance and ease of matching at the board level. The SPB-2026Z features an input power detector, on/off power control, ESD protection, excellent overall robustness, and a hand reworkable and thermally enhanced SOF-26 package.

SPB-2026Z SPECIFICATIONS

Frequency	Gain	ld	NF	Output IP3	P1dB	Vcc
0.7 GHz to 2.2 GHz	13.7 dB	445 mA	5.2 dB	33.8 dBm	25 dBm ¹	5.0

^{1 -} W-CDMA modulation, 64 DPCH overhead, -45 dBc ACPR

FEATURES

- P1 dB = 33.8 dBm at 5 V, 1960 MHz
- ACP = -45 dBc with 25 dBm Ch. Pwr at 1960 MHz
- · On-chip input power detector
- Power up/down control

- · Low thermal resistance package
- · Low power dissipation
- Robust Class 1C ESD
- RoHS and WEEE compliant

